

Vishay Siliconix

# N-Channel 30 V (D-S) MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	30				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0027				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0040				
Q <sub>g</sub> typ. (nC)	17.5				
I <sub>D</sub> (A)	40 <sup>g</sup>				
Configuration	Single				

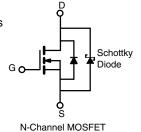
#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- SkyFET<sup>®</sup> with monolithic Schottky diode
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



### **APPLICATIONS**

- · Personal computers and servers
- Synchronous buck
- · Synchronous rectification
- DC/DC conversion



ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSC06DN-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	30	V	
Gate-source voltage		V <sub>GS</sub>	+20, -16	v	
	T <sub>C</sub> = 25 °C		<b>40</b> <sup>g</sup>		
O a 1 a a a data a a a a 1 (T = 450 00)	T <sub>C</sub> = 70 °C		40 <sup>g</sup>		
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	27.6 <sup>a, b</sup>		
	T <sub>A</sub> = 70 °C		25.2 <sup>a, b</sup>		
Pulsed drain current (t = 100 μs)		I <sub>DM</sub>	100	A	
Continuous source-drain diode current	T <sub>C</sub> = 25 °C		<b>40</b> <sup>g</sup>		
	T <sub>A</sub> = 25 °C	I <sub>S</sub>	3.3 <sup>a, b</sup>		
Single pulse avalanche current	1 0.1 ml l	I <sub>AS</sub>	15		
Single pulse avalanche energy  L = 0.1 mH		E <sub>AS</sub>	E <sub>AS</sub> 11.25		
	T <sub>C</sub> = 25 °C		46.3		
Maximum power dissipation	T <sub>C</sub> = 70 °C		29.6	W	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.7 <sup>a, b</sup>		
	T <sub>A</sub> = 70 °C		3.1 <sup>a, b</sup>		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering recommendations (peak temperature) c, d		1	260		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient a, e	t ≤ 10 s	R <sub>thJA</sub>	25	33	°C/W	
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	2.1	2.7	C/VV	

#### Notes

- a. Surface mounted on 1" x 1" FR4 board
- b. t = 10 s
- c. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- e. Maximum under steady state conditions is 81 °C/W
- f. Based on T<sub>C</sub> = 25 °C
- g. Package limited



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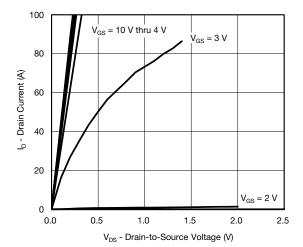
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	•	· · · · · · · · · · · · · · · · · · ·				L	
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-		
Drain-source breakdown voltage (transient) <sup>c</sup>	V <sub>DSt</sub>	V <sub>GS</sub> = 0 V, I <sub>D(aval)</sub> = 15 A, t <sub>transcient</sub> ≤ 50 ns		-	-	٧	
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1	-	2.1		
Gate-source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = +20 V, -16 V	-	-	± 100	nA	
Zana anta unita an dunin anumant		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	-	0.02	0.20	mΛ	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	0.13	1	mA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30	-	-	Α	
Drain acurae en etata registance 3	Б	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	-	0.0022	0.0027	Ω	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	0.0032	0.0040		
Forward transconductance <sup>a</sup>	9fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A	-	120	-	S	
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		-	2455	-		
Output capacitance	Coss			350	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	60	-	1	
C <sub>rss</sub> /C <sub>iss</sub> ratio		]	-	0.025	0.050		
Total gate charge	$Q_g$	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	-	38.5	58		
			-	17.5	27		
Gate-source charge	$Q_{gs}$	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A		6.3	-	nC	
Gate-drain charge	$Q_{gd}$	]	-	2.8	-		
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V	-	29	-		
Gate resistance	$R_g$	f = 1 MHz	0.4	1.15	2	Ω	
Turn-on delay time	t <sub>d(on)</sub>		-	12	24		
Rise time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_L = 1.5 \Omega$	-	14	28	1	
Turn-off delay time	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	23	46		
Fall time	t <sub>f</sub>	]	-	8	16		
Turn-on delay time	t <sub>d(on)</sub>		-	29	58	ns	
Rise time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_L = 1.5 \Omega$	-	50	100	- - -	
Turn-off delay time	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	20	40		
Fall time	t <sub>f</sub>	]	-	9	18		
Drain-Source Body Diode Characteristi	cs						
Continuous source-drain diode current	IS	T <sub>C</sub> = 25 °C	-	-	40	۸	
Pulse diode forward current	I <sub>SM</sub>		-	-	100	Α	
Body diode voltage	$V_{SD}$	I <sub>S</sub> = 5 A, V <sub>GS</sub> = 0 V	-	0.47	0.7	V	
Body diode reverse recovery time	t <sub>rr</sub>		-	31	62	ns	
Body diode reverse recovery charge	$Q_{rr}$	I <sub>F</sub> = 10 A, di/dt = 100 A/μs,	-	19	38	nC	
Reverse recovery fall time	ta	T <sub>J</sub> = 25 °C		16	-		
Reverse recovery rise time	t <sub>b</sub>	7		15	-	ns	

#### **Notes**

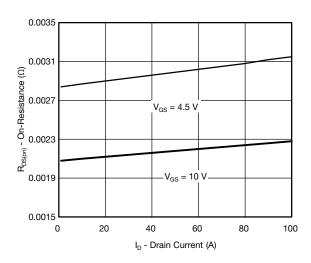
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c.  $T_{CASE} = 25$  °C; Expected voltage stress during 100 % UIS test. Production data log is not available

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

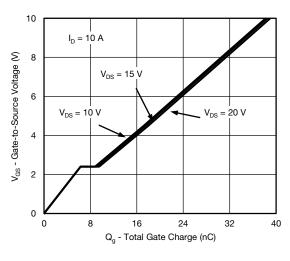




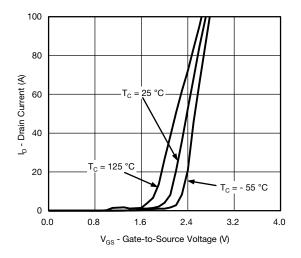
### **Output Characteristics**



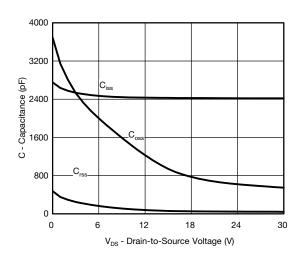
## On-Resistance vs. Drain Current and Gate Voltage



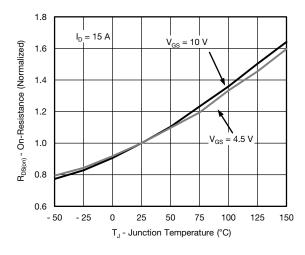
## **Gate Charge**



#### **Transfer Characteristics**

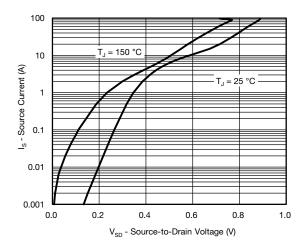


### Capacitance

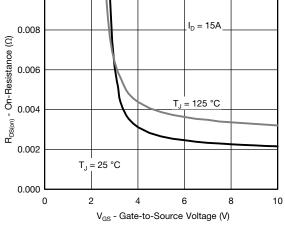


On-Resistance vs. Junction Temperature



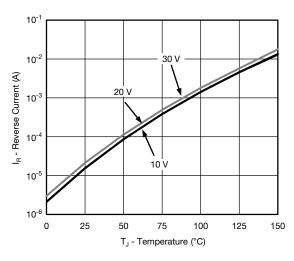


Source-Drain Diode Forward Voltage

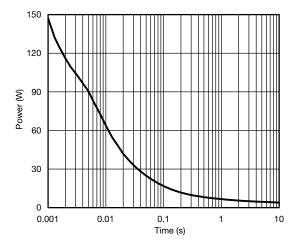


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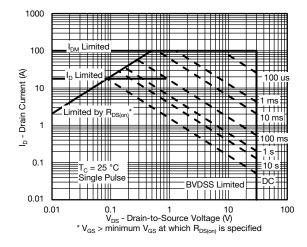
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

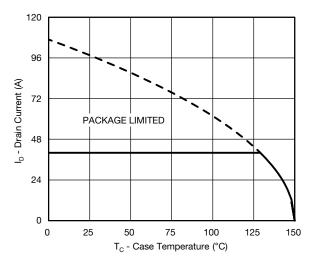


Single Pulse Power, Junction-to-Ambient

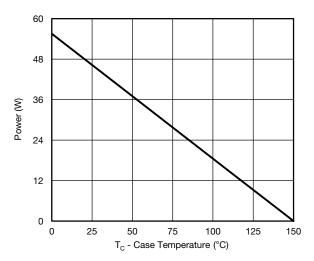


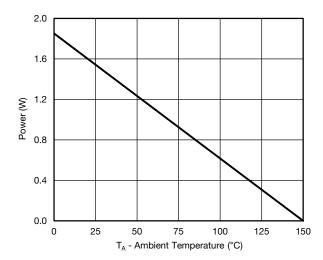
Safe Operating Area, Junction-to-Ambient





#### Current Derating a





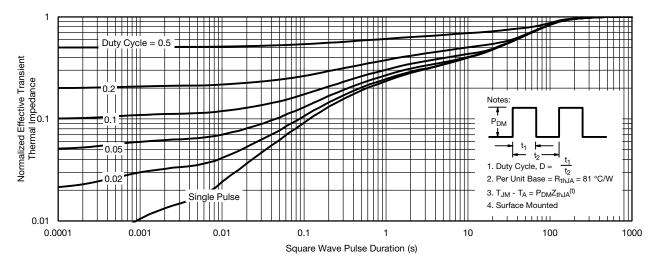
Power, Junction-to-Case

Power, Junction-to-Ambient

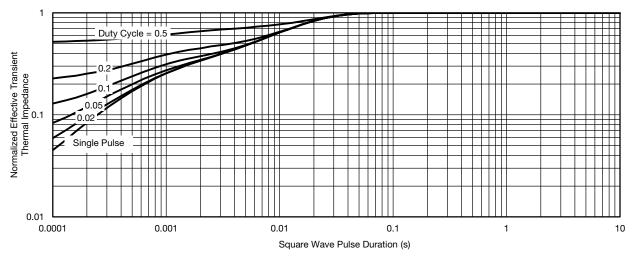
## Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient

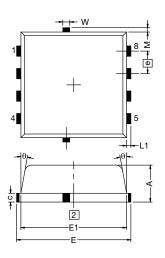


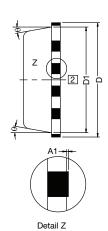
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62944">www.vishay.com/ppg?62944</a>.



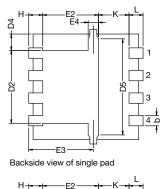
# PowerPAK® 1212-8, (Single / Dual)

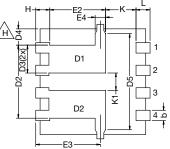




#### Notes

- 1. Inch will govern
- 2 Dimensions exclusive of mold gate burrs
- Dimensions exclusive of mold flash and cutting burrs





Backside view of dual pad

DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D3	0.48	-	0.89	0.019	=	0.035	
D4		0.47 typ.		0.0185 typ			
D5		2.3 typ.		0.090 typ			
Е	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.034 typ.			0.013 typ.		
е		0.65 BSC		0.026 BSC			
K		0.86 typ.			0.034 typ.		
K1	0.35	-	-	0.014	-	-	
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			

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## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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